Physical mechanisms of in situ surface gettering of metals in ribbon silicon for solar cells

D. R. Khana(b) and T. Buonassisi(b)

Department of Materials Science and Engineering, University of California, Berkeley, California 94720 and Materials Science Division, Lawrence Berkeley National Laboratory, Berkeley, California 94720

M. A. Marcus

Advanced Light Source, Lawrence Berkeley National Laboratory, Berkeley, California 94720

A. A. Istratov(c) and E. R. Weber

Department of Materials Science and Engineering, University of California, Berkeley, California 94720 and Materials Science Division, Lawrence Berkeley National Laboratory, Berkeley, California 94720

(Received 13 January 2007; accepted 31 January 2007; published online 7 March 2007)

The authors have employed synchrotron-based x-ray absorption near-edge spectroscopy and x-ray fluorescence microscopy to identify the chemical state and distribution of metals gettered to the surface of String Ribbon silicon grown with CO-ambient gas. Copper and nickel precipitates were observed in their equilibrium silicide phases, indicating a dominant relaxation gettering mechanism. In addition, microwave photoconductive decay measurements show a decrease in bulk iron concentration and a tenfold increase in minority carrier lifetime in CO-ambient grown material. Implications of the observed gettering mechanism on ribbon-type solar cells are discussed. © 2007 American Institute of Physics. [DOI: 10.1063/1.2711523]

An increase in the price of semiconductor-grade silicon resulting from a recent shortage has strongly impacted the solar cell industry and motivated research on reducing material costs. Particularly promising are ribbon-type materials, which by avoiding ingot sawing significantly increase silicon cost competitiveness. Finding methods to increase minority carrier lifetime in ribbon Si grown from solar-grade silicon holds the promise for further cost reductions and reduced supply constraints. Unfortunately, ribbon materials contain local regions of high dislocation density that, in combination with high concentrations of metallic impurities contained in so-called dirty silicon, reduce solar cell efficiencies and limit cost competitiveness. Finding methods to increase minority carrier lifetime in ribbon Si grown from solar-grade silicon materials would be an ideal merger of both advantages.

Ribbon materials offer a unique opportunity to employ creative surface gettering methods to remove metals during growth, as the wafer bulk is never more than a few tens or hundreds of microns from a free surface. Previous studies have shown that the addition of carbon-rich gas into the ambient during growth getters metals to the surface and results in higher minority carrier lifetimes in the bulk. Specifically, the gases create a carbon-rich surface layer with dendritic microdefects on the top surface and a SiC-rich layer up to 1–2 \( \mu \text{m} \) below the surface. It is believed that this SiC layer getters metals, although the exact mechanism is not well understood. Pivac et al. proposed a possible mechanism whereby SiC precipitates act as a sink for silicon self-interstitials (\( \text{Si}_I \)). It is argued that the high flux of \( \text{Si}_I \) towards the SiC-rich area aids the formation of chromium silicide precipitates, which also absorb \( \text{Si}_I \) and continue to stimulate the process.

Nevertheless, certain other impurities also found in silicon solar cell materials do not absorb \( \text{Si}_I \) upon metal silicide formation. NiSi\(_2\) is almost perfectly lattice matched with silicon, and the common copper silicide \( \text{Cu}_3\text{Si} \) ejects copious amounts of \( \text{Si}_I \) into the lattice, the opposite of CrSi\(_2\). These common transition metals are therefore not subject to the mechanism described above and have not been previously investigated in surface gettering experiments. In general, lack of understanding of the chemical state and distribution of the gettered metals has precluded a solid understanding of the mechanisms for the observed gettering.

In this letter, we report on the surface gettering of Cu, Ni, and Fe in String Ribbon material. We elucidate the mechanism of surface gettering by measuring the chemical state and distribution of gettered and ungettered metals in ribbon Si. In addition, we quantify the magnitude of the beneficial effects of in situ surface gettering on String Ribbon grown from a heavily contaminated melt.

Samples of String Ribbon silicon were grown at Evergreen Solar with approximately 840, 220, and 170 ppm weights of Cu, Ni, and Fe, respectively, in the melt. Samples were grown with and without CO gas added to the inert ambient. For each growth condition, a pair of samples was analyzed with and without a 10 \( \mu \text{m} \) silicon etch procedure, to distinguish between metals on the surface and in the bulk. All samples were cleaned in an ultrasonic acetone bath before measurement. The chemical phase and distribution of metals were identified by x-ray absorption near-edge spectroscopy (XANES) and x-ray fluorescence microscopy (\( \mu \)-XRF), respectively, at beamline 10.3.2 of the Advanced Light Source and beamline 20-ID-B of the Advanced Photon Source. XANES spectra were obtained with the sample held at grazing incidence to the beam to maximize fluorescence from metals on the surface.

Figures 1(a) and 1(b) show Cu and Ni XANES spectra from a nonetched sample grown with CO-ambient gas. These are compared with standard spectra of each metal silicide.
and a corresponding oxide. It is clear that both metals precipitated into equilibrium silicide phases: Cu$_3$Si and NiSi$_2$. One can deduce that these metals are precipitated at the sample surface by comparing plane-view μ-XRF maps of Cu for four samples: CO ambient before etching [Fig. 2(a)], CO ambient after etching [Fig. 2(b)], inert ambient before etching [Fig. 2(c)], and inert ambient after etching [Fig. 2(d)]. Comparison of Figs. 2(a) and 2(b) shows that in CO-ambient materials, Cu has been gettered to within at least 10 μm of the surface, consistent with previous secondary ion mass spectroscopy data indicating gettering of Cr to within 1–2 μm of the surface. In contrast, comparison of Figs. 2(c) and 2(d) shows no difference in intensity or distribution of Cu for samples grown in an inert ambient, indicating that no surface gettering took place. Additionally, Fig. 2(a) shows that Cu precipitates on the surface in isolated locations rather than being distributed homogeneously. The μ-XRF maps of Ni fluorescence (not shown) are similar to Fig. 2, indicating that Ni is also gettered by the SiC surface layer and precipitates in isolated locations. No Fe-containing particles were observed above detection limits. This is not surprising, as the solubility of Fe is about two orders of magnitude lower than those of Cu and Ni, and such particles are traditionally more difficult to detect. Streaks of Fe oxide were observed in one nonetched sample grown in CO ambient, but it is unclear whether these were caused by surface contamination after cleaning or persisted through our cleaning procedure.

Minority carrier lifetimes were measured by microwave photoconductive decay (μ-PCD) and compared between an etched sample grown in the inert ambient versus an etched sample grown in a CO-rich ambient (Fig. 3). A significant increase of average minority carrier lifetime, on the order of ten times, is observed in samples grown in the CO-rich ambient. The interstitial Fe concentration was determined by measuring lifetime before and after Fe$_{i}$-B$_{i}$ pair dissociation and is correlated to the measured lifetimes as shown in the inset of Fig. 3. As the CO-ambient sample was etched before measurement, the decrease in Fe$_{i}$-B$_{i}$ concentration suggests that Fe was gettered to the surface during growth.

The observation of Cu and Ni precipitation into their respective equilibrium silicides indicates that gettering occurs through relaxation, whereby supersaturated metal impurities precipitate when provided with energetically favorable nucleation sites. These sites can be structural defects (grain boundaries, dislocations, and voids), regions of favorable point defect concentration, or areas of favorable local strain (compressive or tensile). For example, previous studies have shown that Cu$_3$Si precipitation, which is associated with an atomic volume increase of 50% per metal atom, is accompanied by a variety of strain relaxation phenomena such as elastic deformation and ejection of Si self-interstitials (Si$_i$). SiC precipitation, on the other hand, absorbs Si$_i$, and therefore causes tensile strain. Hence, a possible explanation for
the gettering of Cu is that regions of the material with high SiC content provide the energetically favorable nucleation sites necessary for Cu$_3$Si precipitation via strain compensation through point defects. The spatial inhomogeneity of the gettered Cu observed in Fig. 2(a) further supports evidence for heterogeneous Cu precipitation after supersaturation.

NiSi$_2$, unlike Cu$_3$Si, causes only a 2% (Ref. 9) decrease in atomic volume per metal atom. It can therefore precipitate readily without causing much lattice strain and should not be significantly affected by point defect gradients. However, we do observe thegettering of Ni in XRF maps similar to Fig. 2, while Fig. 1 shows that Ni precipitates as NiSi$_2$. Additionally, the decreased bulk Fe concentration in CO-ambient grown material shown in Fig. 3 indicates that Fe, whose common silicide FeSi$_2$ is associated with a decrease in energy barrier to nucleation.

In summary, a combination of μ-XRF and XANES on String Ribbon silicon grown with CO added to the ambient has elucidated the distribution and chemical state of metals gettered to the surface. We observe silicide precipitate formation of both Cu and Ni, which suggests a dominant relaxation gettering mechanism. The precipitation of metal silicides with different lattice constants relative to Si suggests that the formation of a SiC surface layer creates a variety of energetically favorable nucleation sites for precipitation allowing for the gettering of many different metals. More generally, the observation of a strong influence of ambient gases on metal precipitation and gettering is important and warrants further studies on the effects of other gases on impurities in silicon. Additional understanding of ambient gas effects on silicon defects at high temperatures could provide more options for the successful use of dirty silicon in solar cell manufacturing.

The authors would like to thank Matthew Pickett, Julie Cross, Matthias Heuer, and Sirine Fakra for experimental assistance and helpful discussions. R. L. Wallace, A. Rolke, D. Krauch, T. Ford, and C. Jones are thanked for their assistance in growing the String Ribbon material. The Advanced Light Source is supported by the Director, Office of Science, Office of Basic Energy Sciences, of the U.S. Department of Energy under Contract No. DE-AC02-05CH11231. Use of the Advanced Photon Source was supported by the U.S. Department of Energy, Office of Science, Office of Basic Energy Sciences, under Contract No. DE-AC02-06CH11357.